

DESCRIPTION

MPS4355 is PNP silicon planar epitaxial transistor designed for AF medium power amplifiers.

T0-92



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Collector Current
Continuous Power Dissipation
Operating & Storage Junction Temperature

V_{CEO} 60V
 V_{CBO} 60V
 V_{EBO} 5V
 I_C 1A
 P_d 625mW
 T_j, T_{stg} -55 to +150°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	60		V	$I_C=10\mu\text{A}$ $I_E=0$
Collector-Emitter Breakdown Voltage	LVCEO	60		V	$I_C=10\text{mA}$ $I_B=0^*$
Emitter-Base Breakdown Voltage	BVEBO	5		V	$I_E=10\mu\text{A}$ $I_C=0$
Collector Cutoff Current	ICES		50	nA	$V_{CB}=50\text{V}$ $V_{EB}=0$
D.C. Current Gain	HFE	75			$I_C=500\mu\text{A}$ $V_{CE}=10\text{V}^*$
		75			$I_C=100\text{mA}$ $V_{CE}=10\text{V}^*$
		100	400		$I_C=10\text{mA}$ $V_{CE}=10\text{V}$
		75			$I_C=1\text{mA}$ $V_{CE}=10\text{V}^*$
		60			$I_C=100\mu\text{A}$ $V_{CE}=10\text{V}$



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PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Saturation Voltage	VCE(sat)		0.15	V	IC=150mA IB=15mA*
			0.9	V	IC=500mA IB=50mA*
Base-Emitter Saturation Voltage	VBE(sat)		0.5	V	IC=150mA IB=15mA*
			1.1	V	IC=500mA IB=50mA*
Output Capacitance	Cob		30	pF	VCB=10V f=1MHz
Current Gain-Bandwidth Product	fT	100		MHz	IC=50mA VCE=10V